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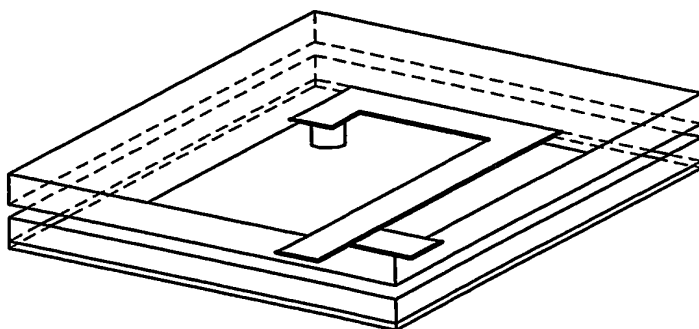
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(54) Title: MULTILAYER STACK WITH COMPENSATED RESONANT CIRCUIT

$$\frac{w}{h_1} > 3 \quad (I)$$



(57) Abstract: A metallization structure in a multilayer stack, which is arranged at a distance from a ground electrode, is characterized in that the metallization structure has a capacitor electrode and a line that acts as a coil, where the capacitor electrode and the line are arranged in a common plane which lies parallel with the ground electrode at a distance h_1 , and in that formula (I) where w is the width of the line.

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